

				Sub	ject	Coc	le: F	COE	2038
Roll No:									

BTECH (SEM III) THEORY EXAMINATION 2021-22 ELECTRONICS ENGINEERING

Time: 3 Hours Total Marks: 100

Note: 1. Attempt all Sections. If require any missing data; then choose suitably.

SECTION A

1. Attempt all questions in brief.

 $2 \times 10 = 20$

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Q no.	Question	Mark	CO
		S	
a.	What you mean by Doping. Describe its need.	2	CO-1
b.	Why Si is preferred as compared to Ge in Semiconductor Electronics.	2	CO-1
c.	Differentiate between Clipper and Clamper circuit.	2	CO-2
d.	Compare LED and photo diode.	2	CO-2
e.	State two Difference between BJT and FET.	2	CO-3
f.	Define Threshold Voltage for an E-MOSFET. Also defineds for an JFET.	2	CO-3
g.	What is unity gain amplifier(buffer)?	2	CO-4
h.	What is SLEW RATE explain briefly?	2	CO-4
i.	Compare analog and digital instruments.	2	CO-5
j.	Write the applications of CRO.	2	CO-5

SECTION B

2. Attempt any three of the following:

Q no.	Question	Marks	CO
a.	Explain Avalanche and Zener Breakdown Mechanism.	10	CO-1
b.	Write a short rote on Tunnel and Varactor Diode.	10	CO-2
c.	Draw the basic structure of Common Base BJT and explain its principle	10	CO-3
	of operation with neat diagram with its input and output characteristics.		
d.	Define Op-Amp with the help of block diagram. List t	h & 0 ide	aCO-4
	characteristic of an Op-Amp. Explain working of Op-Amp as a Adder.		
e.	Draw and explain the block diagram of Digital Storage Oscilloscope	10	CO-5
	(DSO) also compare it with analog oscilloscope.		

SECTION C

3. Attempt any *one* part of the following:

Q no.	Question	Mark	CO
		S	
a.	Draw the V-I characteristics of an ideal & practical diode and explain.	10	CO-1
	Also write the diode equation in support of your answer		
b.	What do you mean by diode resistances? Draw and exp	lalibn t	h€O-1
	characteristics of transition and diffusion capacitance v/s a	pplied	
	voltage.		



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4. Attempt any *one* part of the following:

Q no.	Question	Mark	CO
a.	Determine Iz, I _L , I _R and V _L for the network shown in given fig. $V_{Z} = 10V$ $V_{Z} = 10V$ $V_{Z} = 10V$ $V_{Z} = 10V$	s 10	CO-2
	P _{Z(max)} = 400mW	10	60.2
b.	Determine the output waveform for a given input waveform	10	CO-3

5. Attempt any part of the following:

Q no.	Question	Marks	CO
a.	Distinguish between enhancement type and depletion type MOSFETs.	10	CO-4
	Draw the cross-section of N-channel enhancement MOSFET. Explain		
	and draw the transfer characteristics.		
b.	Describe the construction of a NPN transistor. Define α and β with	10	CO-4
	respect to BJT and derive the relationship between them.		

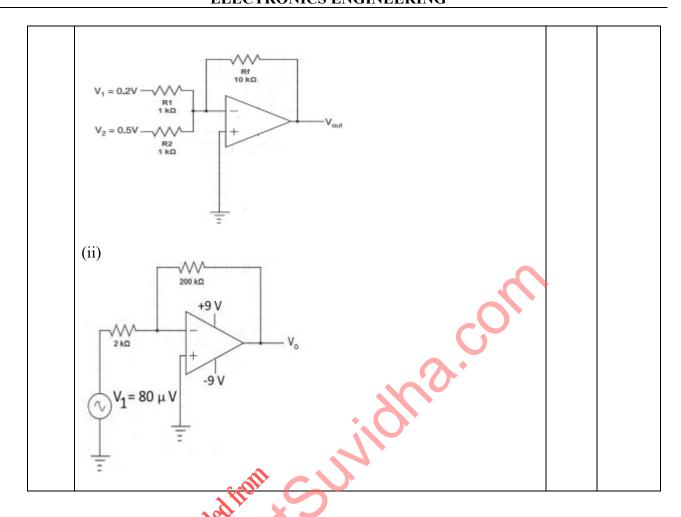
6. Attempt any *one* part of the following:

Q no.	Question	Marks	CO
a.	Explain the concept of Virtual ground. Explain working of Op-Amp as	10	CO-5
	a differentiator.		
b.	Determine the output of following Circuits	10	CO-5
	(i)		



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7. Attempt any one part of the following:

Q no.	Question	Marks	СО
a.	Describe measurement of Voltage, Frequency & Phase using CRO.	10	CO-1
b.	Describe the working of Digital Multimeter with their block diagram.	10	CO-1